BAT54SWT1G

Dual Series Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 Volts (Typ) @ $I_F = 10 \text{ mAdc}$

MAXIMUM RATINGS (T₁ = 125°C unless otherwise noted)

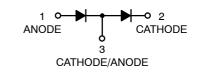
• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

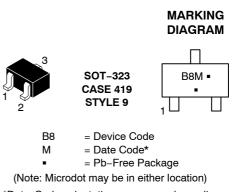
http://onsemi.com

30 VOLT DUAL SERIES SCHOTTKY BARRIER DIODES



Rating	Symbol	Value	Unit		
Reverse Voltage	V _R	30	V		
Forward Power Dissipation @ T _A = 25°C Derate above 25°C	P _F	200 1.6	mW mW/°C		
Forward Current (DC)	١ _F	200 Max	mA		
Non-Repetitive Peak Forward Current t _p < 10 msec	I _{FSM}	600	mA		
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	300	mA		
Junction Temperature	TJ	–55 to 125	°C		
Storage Temperature Range	T _{stg}	–55 to +150	°C		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

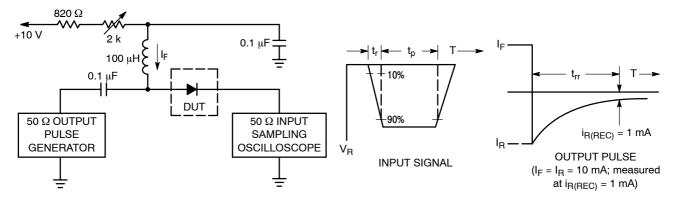
Device	Package	Shipping [†]
BAT54SWT1G	SOT-323 (Pb-Free)	3000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAT54SWT1G

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	30	-	-	V
Total Capacitance (V _R = 1.0 V, f = 1.0 MHz)	CT	-	7.6	10	pF
Reverse Leakage (V _R = 25 V)	۱ _R	-	0.5	2.0	μAdc
Forward Voltage (I _F = 0.1 mAdc)	V _F	-	0.22	0.24	Vdc
Forward Voltage (I _F = 30 mAdc)	V _F	-	0.41	0.5	Vdc
Forward Voltage (I _F = 100 mAdc)	V _F	-	0.52	0.8	Vdc
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}, Figure 1)$	t _{rr}	-	_	5.0	ns
Forward Voltage (I _F = 1.0 mAdc)	V _F	-	0.29	0.32	Vdc
Forward Voltage (I _F = 10 mAdc)	V _F	-	0.35	0.40	Vdc

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so I_{R(peak)} is equal to 10 mA.

3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

BAT54SWT1G

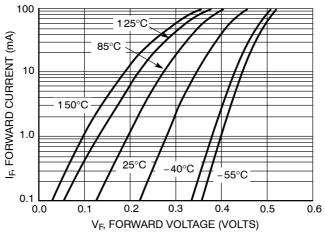


Figure 2. Forward Voltage

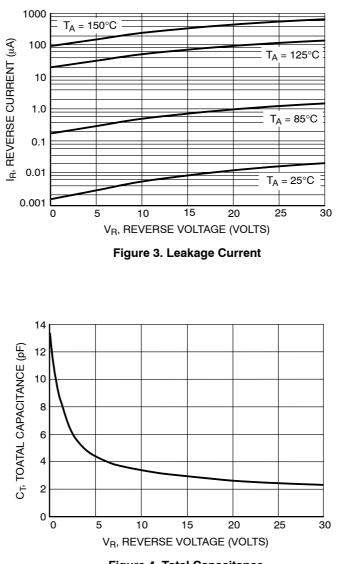
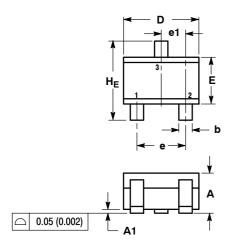


Figure 4. Total Capacitance

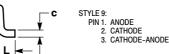
PACKAGE DIMENSIONS

SOT-323 (SC-70) CASE 419-04 ISSUE N

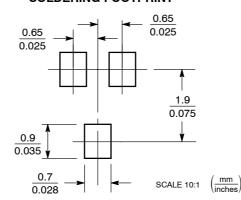


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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